

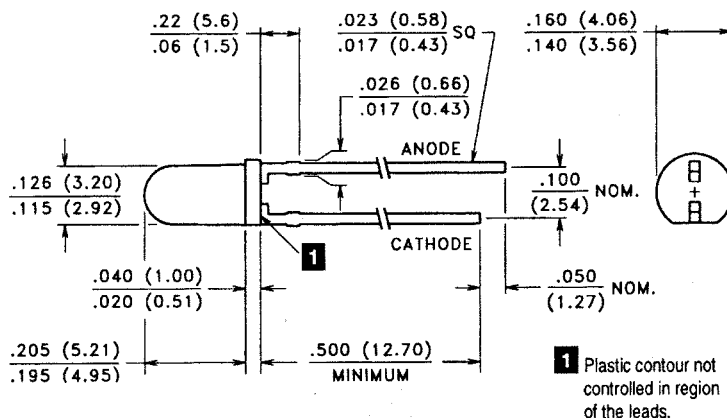
GaAlAs Infrared Emitting Diodes

Long T-1 (3 mm) Plastic Package — 880 nm

VTE3372LA, 74LA



PACKAGE DIMENSIONS inch (mm)



DESCRIPTION

CASE 50A Long T-1 (3 mm)
CHIP SIZE: .011" x .011"

This narrow beam angle 3 mm diameter plastic packaged emitter is suitable for use in optical switch applications. It contains a small area, GaAlAs, 880 nm, high efficiency IRED die.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ $V_R = 5V$:	10 μA
Continuous Power Dissipation:	100 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	1.43 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF
Maximum Continuous Current:	50 mA	Response Time @ $I_F = 20$ mA	
Derate above 30°C:	0.71 mA/°C	Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 μs , 100 pps:	2.5 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-8%/°C	(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V_F	
	E_e		Condition		I_e	P_O	I_{FT}	@ I_{FT}	
	mW/cm ²		distance	Diameter	mW/sr	mW	mA	Volts	Typ.
	Min.	Typ.	mm	mm	Min.	Typ.	(Pulsed)	Typ. Max.	
VTE3372LA	2.0	2.6	10.16	2.1	2.0	3.0	20	1.3 1.8	±10°
VTE3374LA	4.0	5.2	10.16	2.1	4.1	5.0	20	1.3 1.8	±10°

■ Refer to General Product Notes, page 2.